Low Noise Amplifier Chip

AAS2200

Product Specification

V1.1

1. Product Features

Frequency Range: 12~18GHz

Small Signal Gain: 27.5dB

Noise Figure: 0.7dB (Typical)

Output 1dB Compression Point: 2dBm

Bias Conditions: VD = 3.3V, IDQ = 11mA

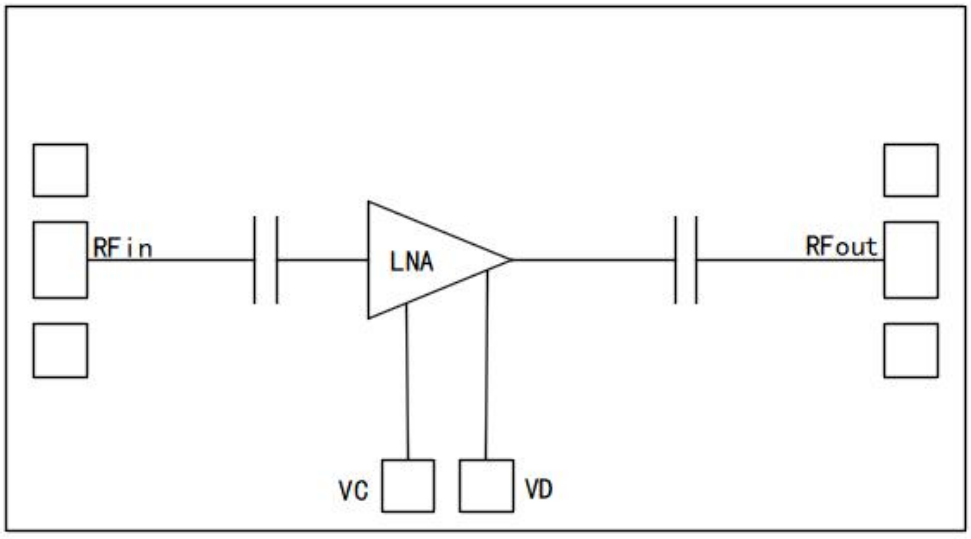
Chip Dimensions: 0.75mm×0.65mm×0.1mm

2. Functional Overview

The AAS2200 is a low noise amplifier chip operating in the 12~18GHz frequency band. Under the operating conditions of +3.3V and 11mA, it provides a gain of 27.5dB, an output 1dB compression point of 2dBm, and a typical noise figure of 0.7dB.

The port impedance of the chip is 50Ω, and the chip adopts backside metal grounding.

3. Functional Block Diagram



4. Typical Applications

Suitable for communication, radar and other application fields.

5. Electrical Performance Parameters

5.1 RF Characteristics

Unless otherwise specified, all electrical characteristics are measured under the following conditions: VD = 3.3V, IDQ = 11mA, small signal input power Pin = -35dBm, ambient temperature TA = +25° C, in a 50Ω system.